

Development of an on-chip Charge Pump in CMOS Technology

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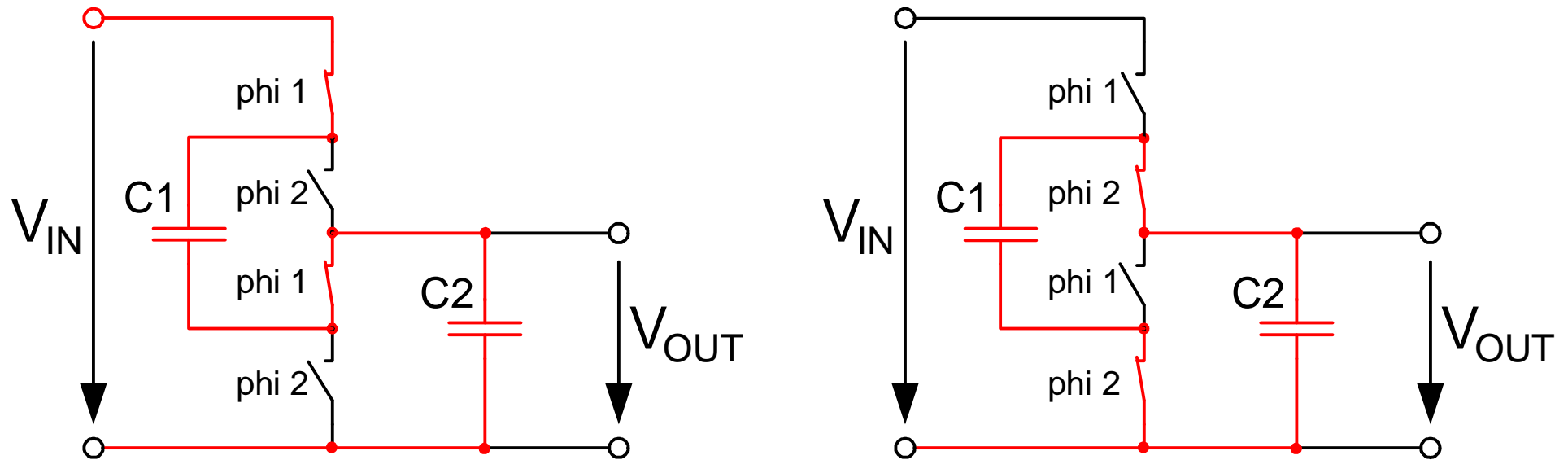
Pixel Replacement/Upgrade Discussion Meeting

9.10.2008

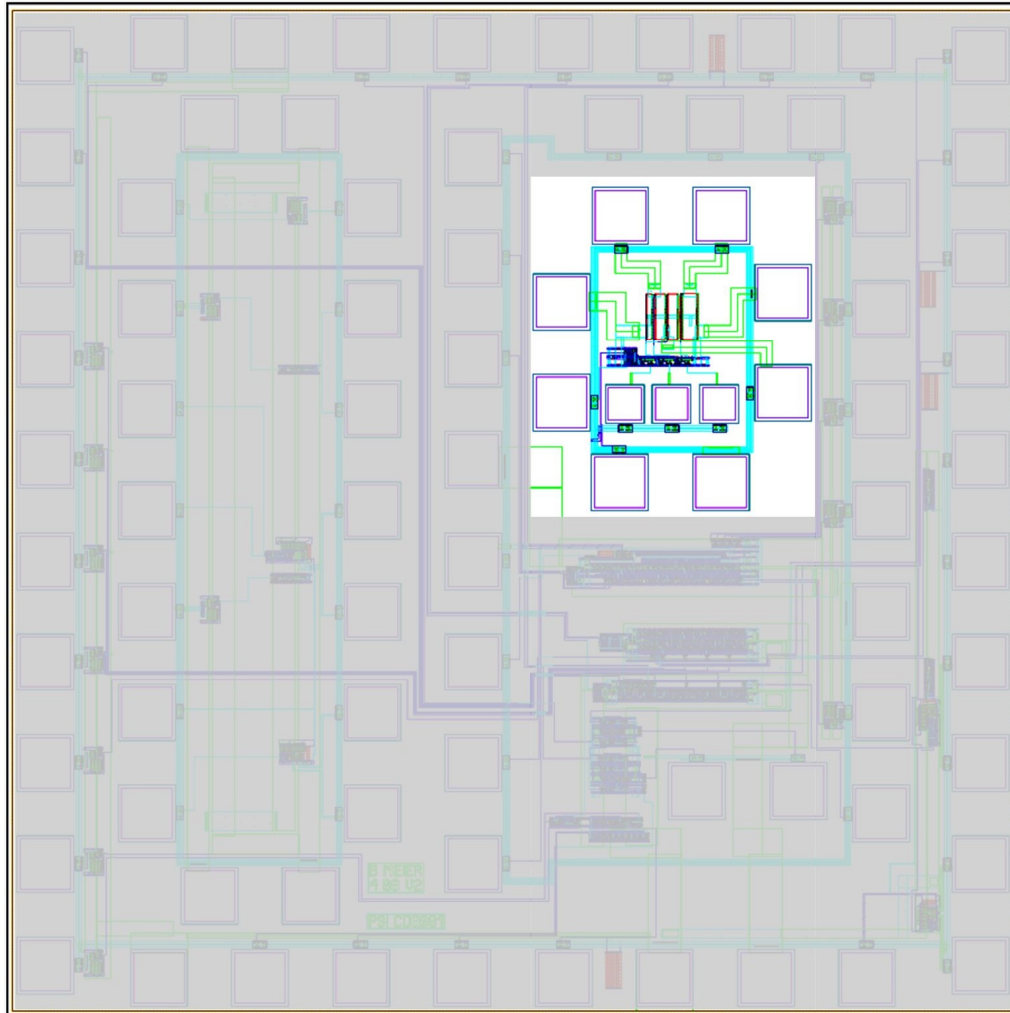
Motivation

- CMS Pixel: two supply voltages $V_{\text{digital}} = 2.0 \dots 2.5\text{V}$ and $V_{\text{analog}} = 1.5\text{V}$ (or lower)
- DC-DC converter for V_{analog} on the Detector Module \rightarrow only one power line
- some free space on an ASIC for data link tests in April 2008
- to learn something about switched capacitor DC-DC converter (area on chip, ...)
- Voltage divider by 2 (simple design)
- for only one CMS Pixel ROC (24 mA)
- switching frequency higher than sensitive frequency range of the ROC ($> 10\text{ MHz}$)

Principle

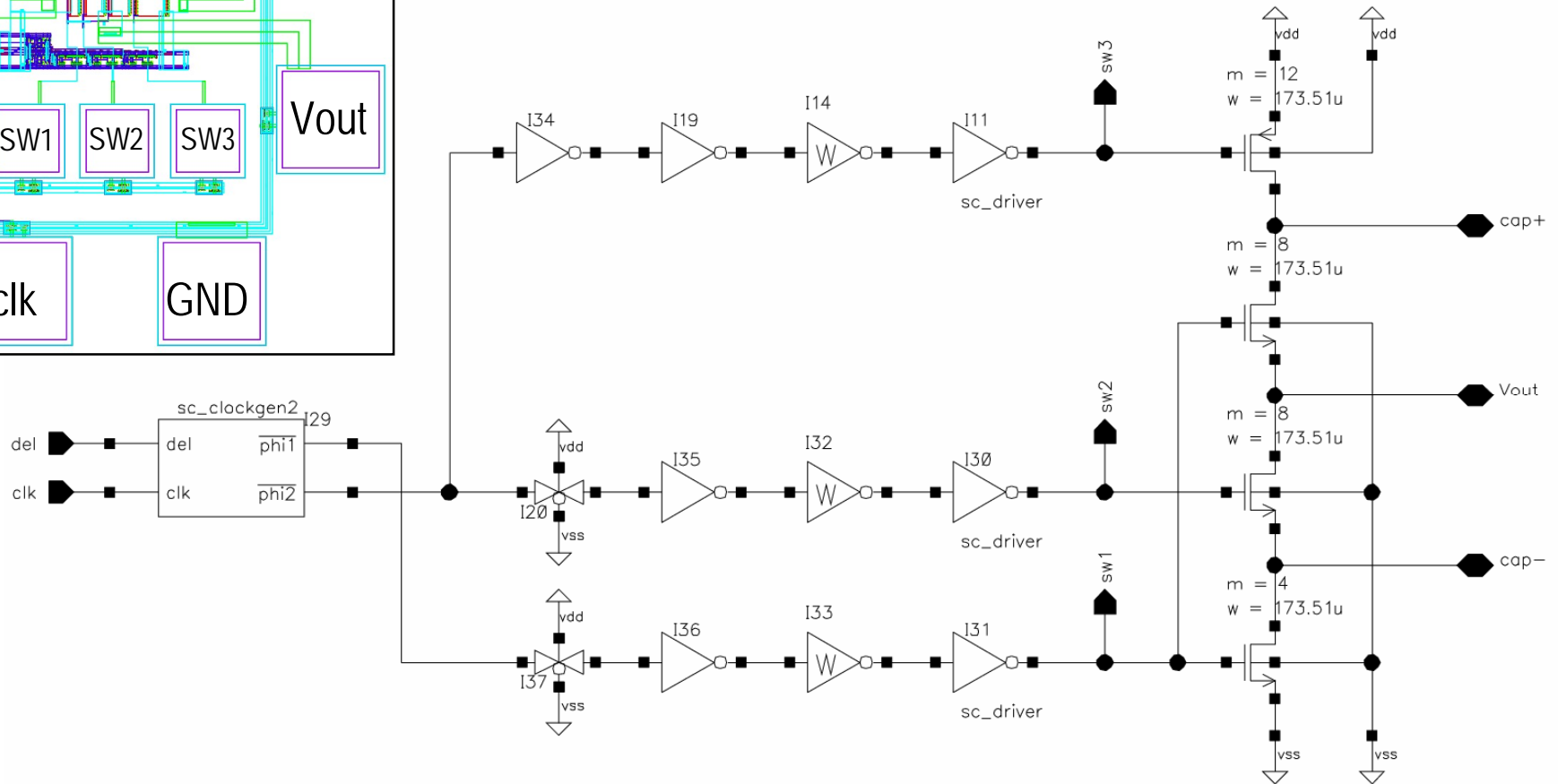
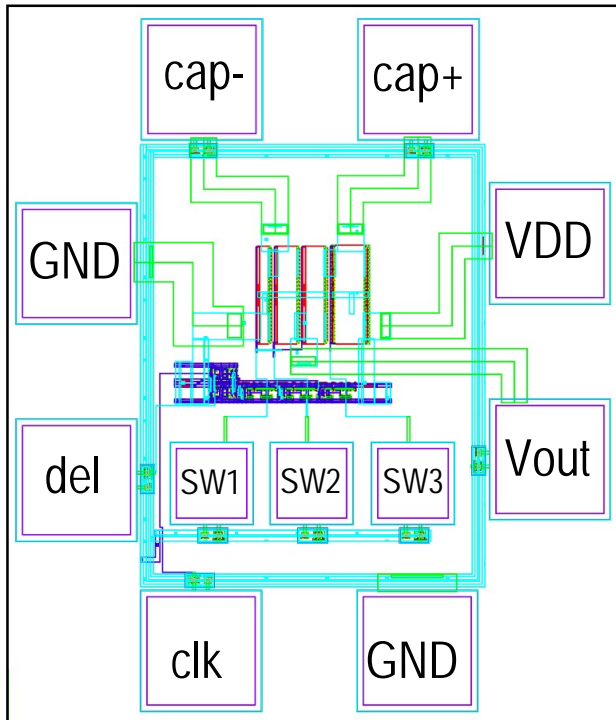


- Voltage divider by 2
- on chip: four switches, two phase generator and drivers
- external oscillator
- external capacitor $C1$ and $C2$ (10 ... 100 nF)

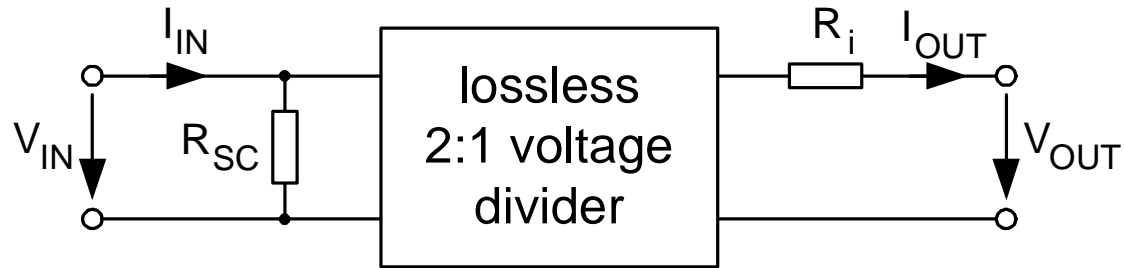


- Size 2 x 2 mm
- Technology: 250 nm CMOS IBM
- Radiation hardness design
- CERN MPW in April 2008
- Samples end of July

Schematic and Layout



Efficiency



Source resistance:
$$R_i = \frac{1}{4} \cdot \frac{1}{fC} \cdot \frac{1 + \exp\left(-\frac{T}{2\tau}\right)}{1 - \exp\left(-\frac{T}{2\tau}\right)}; \quad \tau = 2 R_{ON} C$$

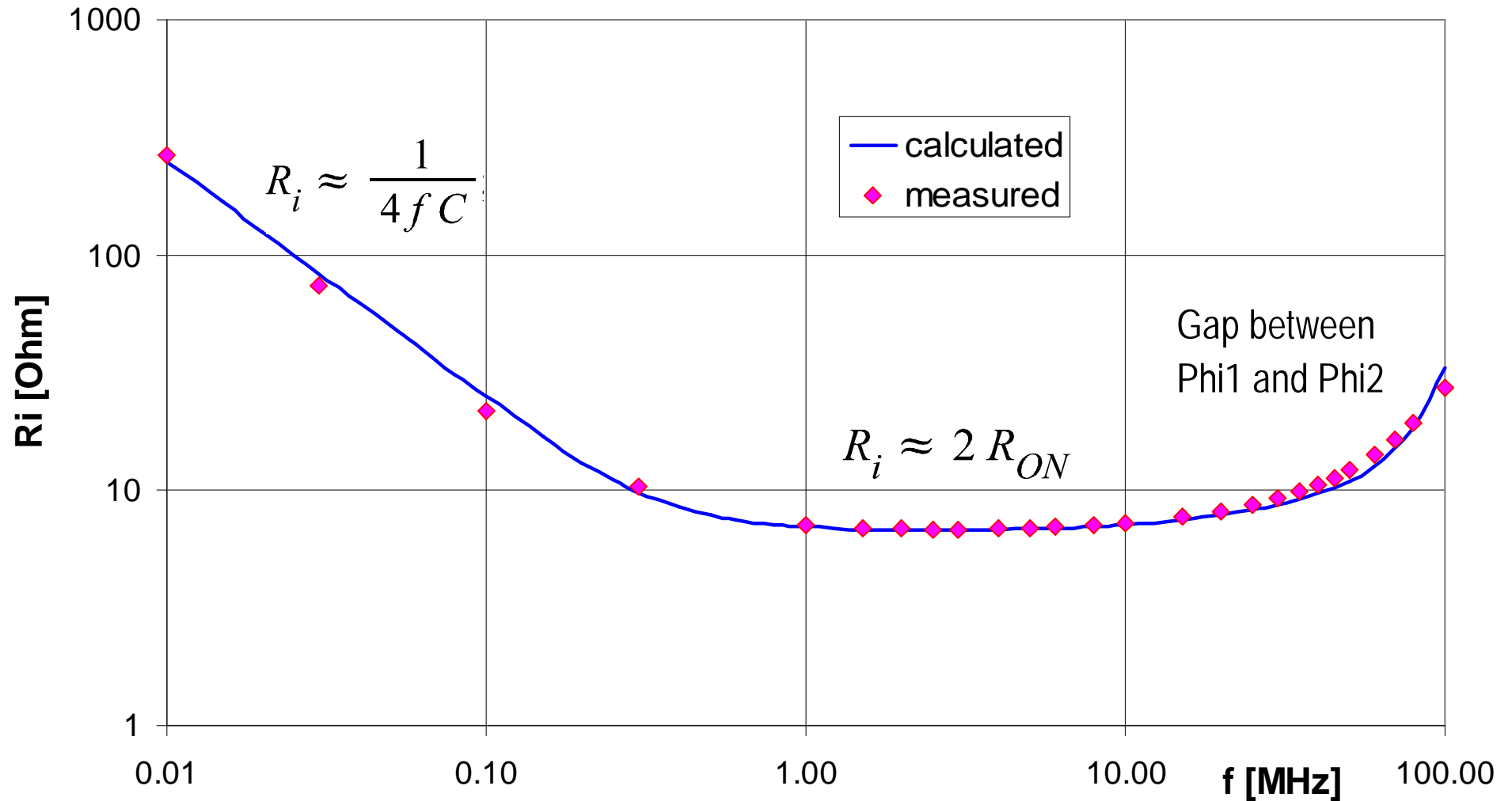
for low frequency:
$$R_i \approx \frac{1}{4fC}; \quad 2\tau \ll T$$

for high frequency:
$$R_i \approx 2 R_{ON}; \quad 2\tau \gg T$$

Gating Loss:
$$P_{SC} = \frac{V_{IN}^2}{R_{SC}} = f C_{SC} V_{IN}^2$$
 Power required to drive the switches

Efficiency:
$$\eta := \frac{P_{OUT}}{P_{IN}} = \frac{V_{OUT} I_{OUT}}{V_{IN} I_{IN} + P_{SC}} = \frac{(V_{IN} - 2 R_i I_{OUT}) I_{OUT}}{V_{IN} I_{OUT} + 2 f C_{SC} V_{IN}}$$

Output Resistance



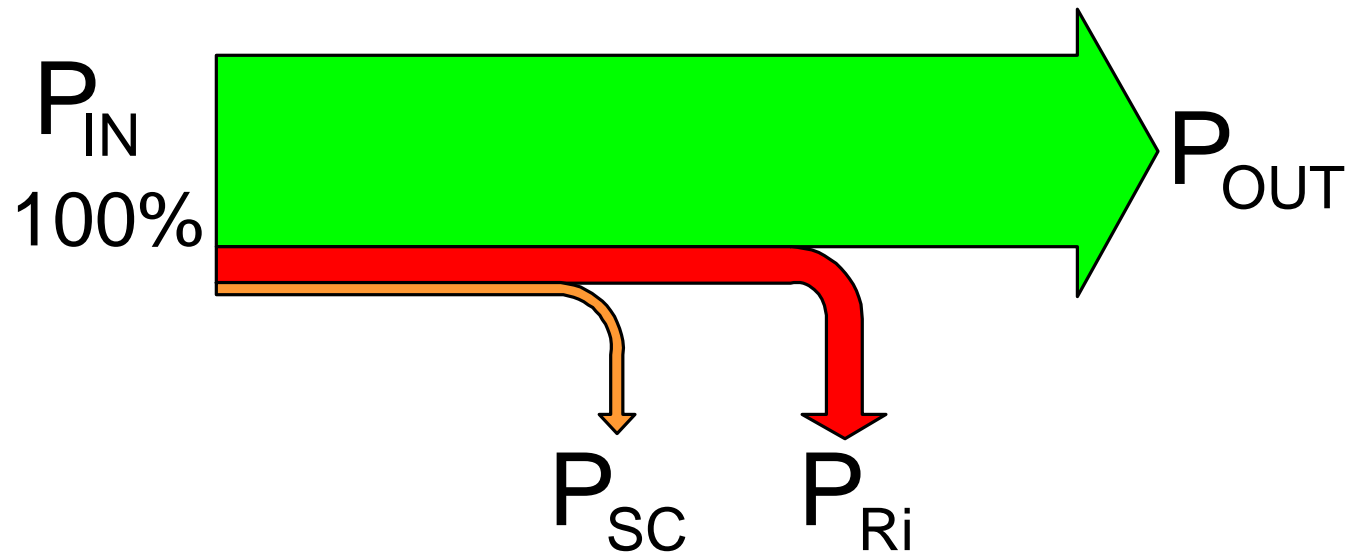
Vin = 2.5V

C = 100 nF

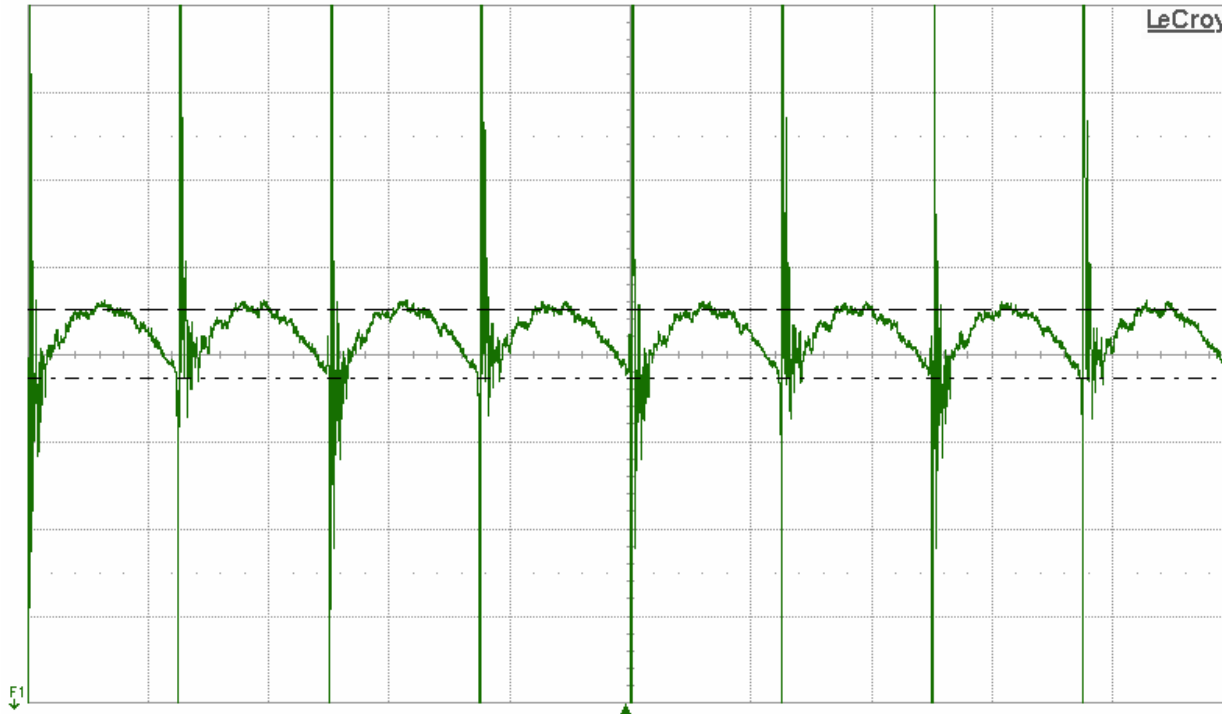
Iout = 24 mA

Ron = 3.3 Ohm

Power Budget



f [MHz]	P_SC	P_Ri	Pout
10	2 %	14 %	84 %
20	4 %	15 %	81 %
40	8 %	18 %	74 %



Output Voltage

200 ns/div

5 mV/div

$f = 4 \text{ MHz}$; $C = 10 \text{ nF}$; $I_{\text{out}} = 25 \text{ mA}$; Ripple: 4 mVpp (smaller at higher freq)

→ ripple is not a problem

spikes ? frequency outside the sensitive frequency range

Summary

- over 80% efficiency at 20 MHz switching frequency
- better efficiency with lower R_{on} → bigger FETs
- area on chip: $10'000 \mu\text{m}^2$ ($100 \mu\text{m} \times 100 \mu\text{m}$)
- output voltage too small ($V_{out} = 1.1\text{V}$ @ $V_{in}=2.5\text{V}$ and $I_{out} = 24 \text{ mA}$)
- not adjustable, no voltage regulation

to do

- test of the SC-regulator together with the ROC (noise)

possible configurations

- one small (24mA) regulator per ROC → advantage: adjustable for each ROC
- or one big regulator per module (=16 ROCs) → less external capacitors

no concrete plan for future projects

- 3:2 voltage converter
- scale-up for 16 ROCs
- adjustable